Walter E Henderson

List of Publications by Year
in descending order

31	407	840776 11	752698 20
papers	citations	h-index	g-index

31	31	31	568
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Spatially resolved 3D metabolomic profiling in tissues. Science Advances, 2021, 7, .	10.3	29
2	Strain relaxation via formation of cracks in compositionally modulated two-dimensional semiconductor alloys. Npj 2D Materials and Applications, 2018, 2, .	7.9	23
3	Characterization and Simulation of Permittivity Enhancements of Si<inf>O2</inf>/Si<inf>3</inf>N<inf>4</inf> Nanolaminate Layers. , 2018, , .		0
4	ALD TiOxas a top-gate dielectric and passivation layer for InGaZnO115ISFETs. Semiconductor Science and Technology, 2017, 32, 114004.	2.0	4
5	A mechanistic study of the interaction of water-soluble borate glass with apatite-bound heterocyclic nitrogen-containing bisphosphonates. Acta Biomaterialia, 2016, 31, 339-347.	8.3	5
6	Impact of Microstructure on Dielectric Nanocomposites With High-<italic>k</italic> Interfacial Layers. IEEE Nanotechnology Magazine, 2015, 14, 717-725.	2.0	1
7	Using a university characterization facility to educate the public about microscopes: light microscopes to SEM. , 2015, , .		0
8	Fractal Electrode Formation in Metalâ€“Insulator Composites Near the Percolation Threshold. IEEE Nanotechnology Magazine, 2013, 12, 725-733.	2.0	4
9	In situ Auger probe enabling epitaxy composition control of alloys by elemental surface analysis. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 03C126.	1.2	2
10	Halide based MBE of crystalline metals and oxides. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 155-160.	0.8	20
11	A versatile metal-halide vapor chemistry for the epitaxial growth of metallic, insulating and semiconducting films. Journal of Crystal Growth, 2011, 324, 134-141.	1.5	17
12	Growth kinetics of AlxGa1â€“xN grown via ammonia-based metal-organic molecular beam epitaxy. Journal of Crystal Growth, 2010, 312, 209-212.	1.5	3
13	High-Temperature Growth of GaN and Al x Ga1â^'x N via Ammonia-Based Metalorganic Molecular-Beam Epitaxy. Journal of Electronic Materials, 2010, 39, 473-477.	2.2	0
14	Complementary oxide memristor technology facilitating both inhibitory and excitatory synapses for potential neuromorphic computing applications. , 2009, , .		12
15	Extremely high hole concentrations in câ€plane GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S788.	0.8	27
16	Growth and characterization of AlxGa1â^'xN via NH3-based metal-organic molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1328-1332.	1.5	6
17	Transient atomic behavior and surface kinetics of GaN. Journal of Applied Physics, 2009, 106, .	2.5	41
18	Investigation into the use of molecular hydrogen on the growth of gallium nitride via metal-organic molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1723-1725.	0.8	1

#	Article	IF	Citations
19	Mixed alkyl exchange and exploitable surface interactions in InGaN by NH3-based metal organic molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 5297-5302.	1.5	4
20	Reclamation of a molecular beam epitaxy system and conversion for oxide epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 1501-1506.	2.1	0
21	InN: A material with photovoltaic promise and challenges. Journal of Crystal Growth, 2006, 288, 218-224.	1.5	82
22	An investigation of the effects of radiation exposure on stability constraints in epitaxial SiGe strained layers. Solid-State Electronics, 2006, 50, 1194-1200.	1.4	1
23	Influence of growth conditions and surface reaction byproducts on GaN grown via metal organic molecular beam epitaxy: Toward an understanding of surface reaction chemistry. Journal of Electronic Materials, 2006, 35, 562-567.	2.2	7
24	Molecular Beam Epitaxy of Lithium Niobate Multifunctional Materials Using a Chloride Refractory Metal Chemistry. ECS Transactions, 2006, 2, 103-114.	0.5	3
25	Mg doped GaN using a valved, thermally energetic source: enhanced incorporation, and control. Journal of Crystal Growth, 2005, 279, 26-30.	1.5	18
26	Growth of InN on Ge substrate by molecular beam epitaxy. Journal of Crystal Growth, 2005, 279, 311-315.	1.5	14
27	Molecular beam epitaxy of complex metal-oxides: Where have we come, where are we going, and how are we going to get there?. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1272.	1.6	32
28	III-nitride integration on ferroelectric materials of lithium niobate by molecular beam epitaxy. Applied Physics Letters, 2005, 87, 171107.	3.3	34
29	Mg Doped GaN Using a Valved, Thermally Energetic Source: Enhanced Incorporation, Control and Quantitative Optimization. Materials Research Society Symposia Proceedings, 2003, 798, 719.	0.1	4
30	III-Nitride Growth on Lithium Niobate: A New Substrate Material for Polarity Engineering in III-Nitride Heteroepitaxy. Materials Research Society Symposia Proceedings, 2002, 743, L1.4.1.	0.1	11
31	Molecular Beam Epitaxial Growth of AlN/GaN Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 2002, 743, L6.2.1.	0.1	2